



N-Channel 60-V (D-S) Fast Switching MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
60	0.0083 at $V_{GS} = 10 \text{ V}$	19.3	105		

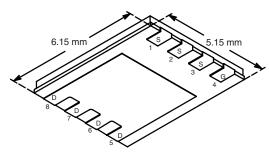
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®]
 Package with Low 1.07 mm Profile
- 100 % R_g Tested
- High Threshold Voltage At High Temperature





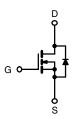
PowerPAK SO-8



Bottom View

Ordering Information: Si7452DP-T1-E3 (Lead (Pb)-free)

Si7452DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T,I = 150 °C) ^a	T _A = 25 °C	I _D	19.3	11.5	
Continuous Diain Current (1) = 150 °C)	T _A = 70 °C		15.5	9.2	
Pulsed Drain Current		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.6	
Avalanche Current		I _{AS}	40		
Avalanche Energy		E _{AS}	80		mJ
Mariana Damar Dissipational	T _A = 25 °C	P _D	5.4	1.9	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.4	1.2	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lunction to Ambienta	t ≤ 10 s	R _{thJA}	18	23	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		52	65		
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.3		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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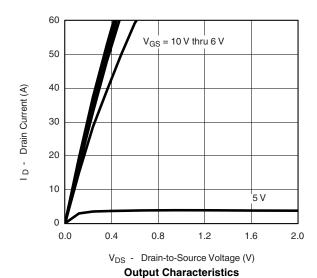
Parameter Symbol		Test Condition	Min.	Тур.	Max.	Unit
Static				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.4		4.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
7 0	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	
Zero Gate Voltage Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 19.3 A		0.007	0.0083	Ω
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_D = 19.3 \text{ A}$		51		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 4.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V
Dynamic ^b	L					
Total Gate Charge	Qg			105	160	nC
Gate-Source Charge	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 19.3 \text{ A}$		40		
Gate-Drain Charge	Q _{gd}			21		
Gate Resistance	R_g	f = 1 MHz	0.5	1.0	1.5	Ω
Turn-On Delay Time	t _{d(on)}			45	70	
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		15	25	ns
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		90	135	
Fall Time	t _f			40	60	113
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 4.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		46	70	

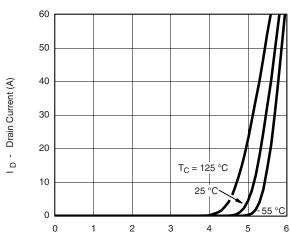
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





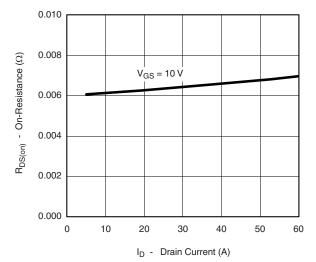
V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**



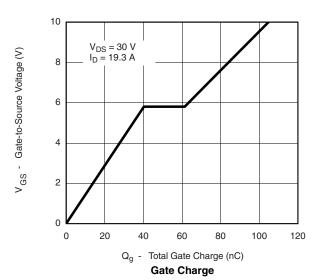


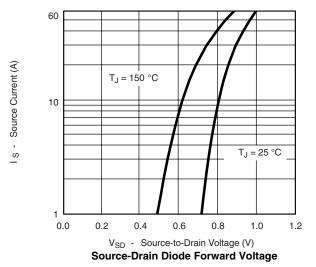


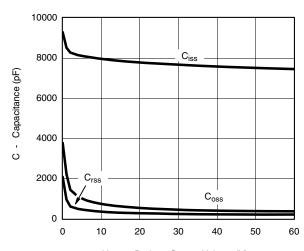
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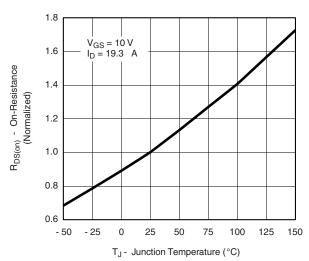
On-Resistance vs. Drain Current



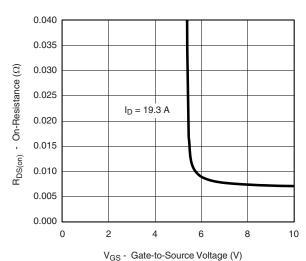




V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature

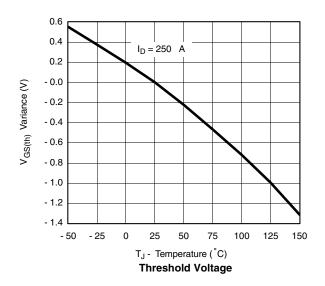


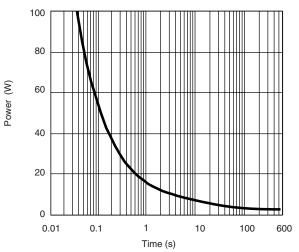
On-Resistance vs. Gate-to-Source Voltage

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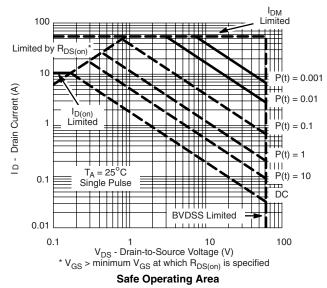
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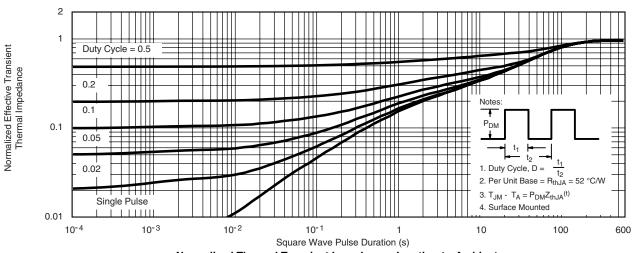
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

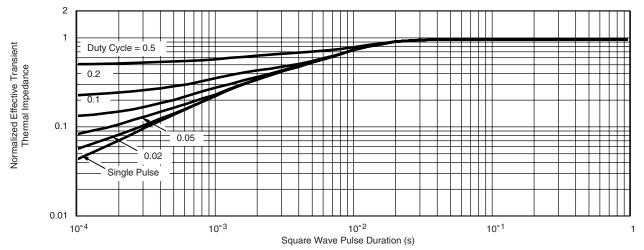




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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